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(71) Applicant (for all designated States except US): **MI-CRON TECHNOLOGY, INC.** [US/US]; 8000 S. Federal Way, Boise, ID 83707-0006 (US).

(72) Inventor; and

(75) Inventor/Applicant (for US only): **LIU, Jun** [CN/US]; 1041 S. Dale Street, Apt. 101, Boise, ID 83706 (US).

(74) Agents: **LIANG, Chen** et al.; Perkins Coie LLP, P.O. Box 1247, Seattle, WA 98111-1247 (US).

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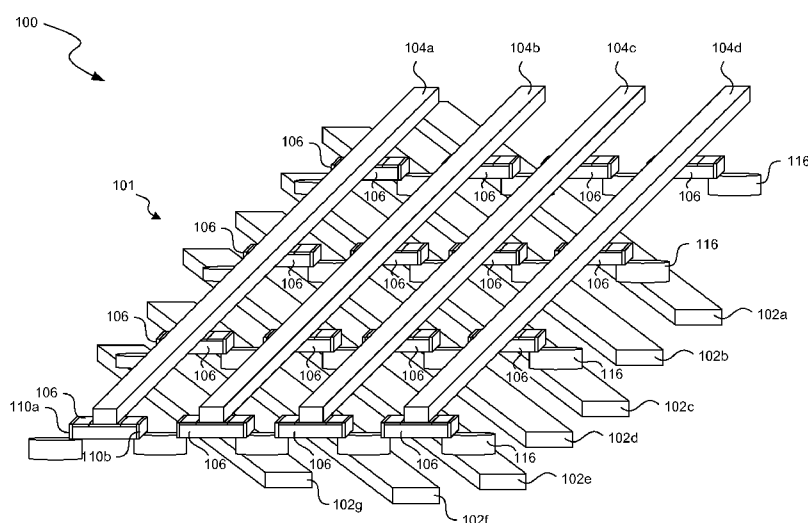


FIG. 2

(57) Abstract: Memory arrays and associated methods of manufacturing are disclosed herein. In one embodiment, a memory array includes an access line extending along a first direction and a first contact line and a second contact line extending along a second direction different from the first direction. The first and second contact lines are generally parallel to each other. The memory array also includes a memory node that includes a first memory cell electrically connected between the access line and the first contact line to form a first circuit, and a second memory cell electrically connected between the access line and the second contact line to form a second circuit different from the first circuit.

